Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	82515	trench$2	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 10:58
L2	110266	memory near2 cell$1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 10:58
L3	886	buried adj2 strap$1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 10:59
L4	228219	(isolat$3 near2 trench$2) or sti	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 10:59
L5	1733	deep with capacitor$1 with 1	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:06
L6	481133	(silicon or semiconduct$3) near10 (substrate$1 or wafer$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:07
L7	137392	polysilicon or polysi or poly-si or (polycrystalline adj (silicon or si))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:07
L8	165050	diffus$3 same (heat$3 or anneal$3 or thermal$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:08
L9	106	3 same 7 same 8	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:08
L10	40838	2 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:09

L11	45	4 and 5 and 9 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:09
L12	2697	mask$3 with lines with spaces	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:10
L13	4	12 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:21
L14	41	11 not 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/20 11:24